

INCHANGE Semiconductor

isc Product Specification

isc Silicon NPN Power Transistors

MJ13070/13071

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 400V(\text{Min})$ —MJ13070
= $450V(\text{Min})$ —MJ13071
- High Switching Speed

APPLICATIONS

- Designed for high-voltage ,high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line operated switch-mode applications.

Typical applications:

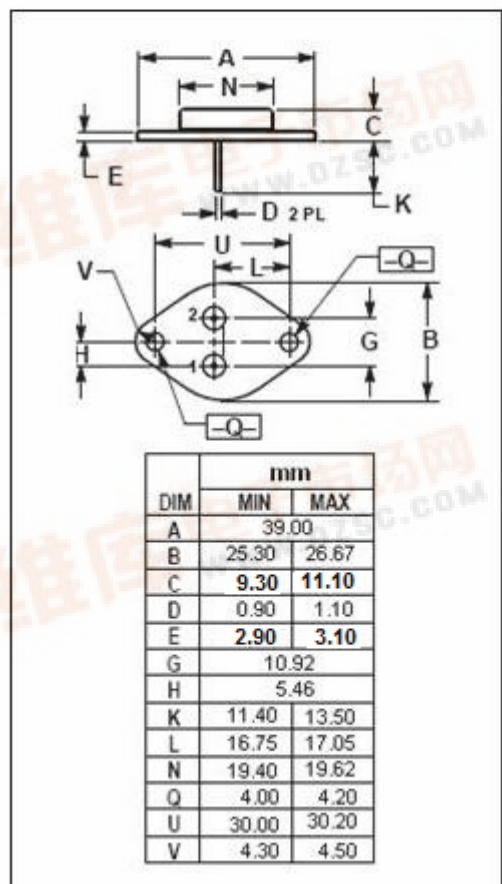
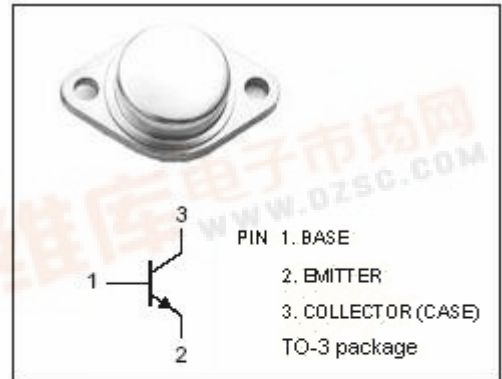
- Switching regulators
- Inverters
- Solenoid and relay drivers
- Motor controls
- Deflection circuits

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage	MJ13070	650
		MJ13071	750
$V_{CEO(SUS)}$	Collector-Emitter Voltage	MJ13070	400
		MJ13071	450
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	8	A
I_B	Base Current-Continuous	2	A
I_{BM}	Base Current-Peak	4	A
P_C	Collector Power Dissipation@ $T_C=25^\circ\text{C}$	125	W
T_J	Junction Temperature	200	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	1.4	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	MJ13070	$I_C=100\text{mA}$; $I_B=0$	400			V
		MJ13071		450			
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage		$I_C=3\text{A}$; $I_B=0.6\text{A}$ $I_C=3\text{A}$; $I_B=0.6\text{A}$; $T_C=100^{\circ}\text{C}$			1.0 2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage		$I_C=5\text{A}$; $I_B=1\text{A}$			3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage		$I_C=3\text{A}$; $I_B=0.6\text{A}$ $I_C=3\text{A}$; $I_B=0.6\text{A}$; $T_C=100^{\circ}\text{C}$			1.5 1.5	V
I_{CEV}	Collector Cutoff Current	MJ13070	$V_{CEV}=650\text{V}$; $V_{BE(off)}=1.5\text{V}$ $V_{CEV}=650\text{V}$; $V_{BE(off)}=1.5\text{V}$; $T_C=100^{\circ}\text{C}$			0.5 2.5	mA
		MJ13071	$V_{CEV}=750\text{V}$; $V_{BE(off)}=1.5\text{V}$ $V_{CEV}=750\text{V}$; $V_{BE(off)}=1.5\text{V}$; $T_C=100^{\circ}\text{C}$			0.5 2.5	
I_{CER}	Collector Cutoff Current	MJ13070	$V_{CE}=650\text{V}$; $R_{BE}=50\Omega$, $T_C=100^{\circ}\text{C}$			3.0	mA
		MJ13071	$V_{CE}=750\text{V}$; $R_{BE}=50\Omega$, $T_C=100^{\circ}\text{C}$			3.0	
I_{EBO}	Emitter Cutoff Current		$V_{EB}=6\text{V}$; $I_C=0$			1.0	mA
h_{FE}	DC Current Gain		$I_C=3\text{A}$; $V_{CE}=5\text{V}$	8			
C_{OB}	Output Capacitance		$I_E=0$; $V_{CB}=10\text{V}$; $f_{\text{test}}=1.0\text{kHz}$			250	pF

Switching times;Resistive Load

t_d	Delay Time	$I_C=3\text{A}$, $V_{CC}=250\text{V}$; $I_{B1}=0.4\text{A}$; $t_p=30\mu\text{s}$; $V_{BE(off)}=5\text{V}$ Duty Cycle $\leq 2.0\%$		30	50	ns
t_r	Rise Time			100	400	ns
t_s	Storage Time			400	1500	ns
t_f	Fall Time			175	500	ns